IN THE CLAIMS:

Please amend the claims as follows:

1-24. (Withdrawn)

25-49. (Canceled)

50. (Currently Amended) A method of manufacturing a device comprising the steps of:

forming a thin film transistor ~~formed~~ over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming a wiring over the interlayer insulating film;

forming a pixel electrode ~~connecting~~ connected to the wiring with the thin film transistor, over the interlayer insulating film;

forming a resin insulating film over the wiring, the pixel electrode, and the interlayer insulating film;

after forming the resin insulating film, forming a protective film over the resin insulating film;

after forming the protective film, moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room;

after moving the substrate, removing the protective film;

after removing the protective film, forming a bank by etching the resin insulating film ~~to expose said pixel electrode~~;

after forming the bank, forming a light emitting layer over said pixel electrode ~~after said etching~~ and the bank,

wherein said steps of removing, ~~etching~~ forming the bank, and forming [[a]] the light emitting layer are performed in said second processing room.

51. (Previously presented) A method of manufacturing a device according to claim 50, wherein the pixel electrode is an anode or a cathode.

52. (Currently Amended) A method of manufacturing a device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming a wiring over the interlayer insulating film;

forming a pixel electrode ~~connecting~~ connected to the wiring with the thin film transistor, over the interlayer insulating film;

forming a resin insulating film over the wiring, the pixel electrode and the interlayer insulating film;

after forming the resin insulating film, forming a protective film for preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

~~removing the protective film;~~

~~etching the resin insulating film to expose said pixel electrode;~~

~~forming a light emitting layer over said pixel electrode~~

after forming the protective film, moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room.

53. (Canceled)

54. (Previously presented) A method of manufacturing a device according to claim 52, wherein the protective film for preventing the substrate from contamination and electrostatic discharge damage is an organic conductive material selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkylmonoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate, alkylbenzenesulfonate, alkyl phosphate,

tetraalkylammonium salt, trialkylbenzylammonium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl ether.

55. (Previously presented) A method of manufacturing a device according to claim 54, wherein the protective film for preventing the substrate from contamination and electrostatic discharge damage is an organic conductive material is formed by spin coating or evaporation.

56. (Previously presented) A method of manufacturing a device according to claim 52, wherein the protective film for preventing the substrate from contamination and electrostatic discharge damage comprises an organic insulating material selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

57-61. (Canceled)

62. (Currently Amended) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming a wiring over the interlayer insulating film;

forming a pixel electrode ~~connecting~~ connected to the wiring over the interlayer insulating film;

forming a resin insulating film over the wiring, the pixel electrode and the interlayer insulating film; and

after forming the resin insulating film, forming a film over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

after forming the film, moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room,

after moving the substrate, removing the film;

after removing the film, forming a bank by etching the resin insulating film ~~to expose said pixel electrode~~;

after forming the bank, forming a light emitting layer over said pixel electrode ~~after said etching~~ and the bank,

wherein said steps of removing, etching and forming [[a]] the light emitting layer are performed in said second processing room.

63. (Currently Amended) A method of manufacturing a light emitting device according to claim 62, wherein the film over the resin insulating film comprises an organic conductive material selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkyl monoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate, alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzylammonium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

64. (Previously presented) A method of manufacturing a light emitting device according to claim 62, wherein the film comprises an organic insulating material selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

65. (Currently Amended) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming a wiring over the interlayer insulating film;

forming a pixel electrode ~~connecting~~ connected to the wiring over the interlayer insulating film;

forming a resin insulating film over the wiring, the pixel electrode, and the interlayer insulating film;

after forming the resin insulating film, forming a film over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

after forming the film, moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room;

after moving the substrate, removing the film;

after removing the film, forming a bank by etching the resin insulating film ~~to form a bank~~;

baking the bank in a vacuum;

forming an organic compound layer over the bank and the ~~first~~ pixel electrode;

forming a second electrode on the organic compound layer.

66. (Currently Amended) A method of manufacturing a light emitting device according to claim 65, wherein the film over the resin insulating film comprises an organic conductive material selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkyl monoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate, alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzylammonium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

67. (Currently Amended) A method of manufacturing a light emitting device according to claim 65, wherein the film over the resin insulating film comprises an organic insulating material selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

68. (Currently Amended) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming a wiring over the interlayer insulating film;

forming a pixel electrode ~~connecting~~ connected to the wiring over the interlayer insulating film;

forming a resin insulating film over the wiring, the pixel electrode and the interlayer insulating film;

after forming the resin insulating film over the wiring, the pixel electrode and the interlayer insulating film, forming a film comprising ~~an organic~~ a conductive material over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

after forming the film, moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room,

~~wherein the pixel electrode and the wiring are covered with the resin insulating film without being in contact with the film~~ wherein in the step of moving, the resin insulating film prevents the film from contacting with the wiring, the pixel electrode and the interlayer insulating film.

69. (Currently Amended) A method of manufacturing a light emitting device according to claim 68, wherein the ~~organic~~ conductive material is selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkyl monoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate, alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzylammonium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

70. (Currently Amended) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming a wiring over the interlayer insulating film;

forming a pixel electrode ~~connecting~~ connected to the wiring over the interlayer insulating film;

forming a resin insulating film over the wiring, the pixel electrode, and the interlayer insulating film; and

after forming the resin insulating film over[[,]] the wiring, the pixel electrode, and the interlayer insulating film, forming a film comprising ~~an organic~~ conductive material over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

after forming the film comprising the organic conductive material, moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room.

71. (Currently Amended) A method of manufacturing a light emitting device according to claim 70, wherein the ~~organic~~ conductive material is selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkyl monoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate, alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzylammonium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

72. (Currently Amended) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming a wiring over the interlayer insulating film;

forming a ~~first~~ pixel electrode ~~connecting~~ connected to the wiring over the interlayer insulating film;

forming a resin insulating film over the wiring, the ~~first~~ pixel electrode, and the interlayer insulating film;

after forming the resin insulating film over, the wiring, the ~~first~~ pixel electrode, and the interlayer insulating film, forming a film comprising ~~an organic~~ a conductive material over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

after forming the film comprising the organic conductive material, moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room;

after moving the substrate, removing the film;

after removing the film, forming a bank by etching the resin insulating film ~~to form a bank~~;

baking the bank in a vacuum;

forming an organic compound layer over the bank and the ~~first~~ pixel electrode;

forming a second electrode on the organic compound layer.

73. (Currently Amended) A method of manufacturing a light emitting device according to claim 72, wherein the ~~organic~~ conductive material is selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkyl monoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate, alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt,

trialkylbenzylammonium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

74. (Currently Amended) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming a wiring over the interlayer insulating film;

forming a pixel electrode ~~connecting~~ connected to the wiring over the interlayer insulating film;

forming a resin insulating film over the wiring, the pixel electrode, and the interlayer insulating film;

after forming the resin insulating film, forming a film comprising an ~~organic~~ insulating material over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

after forming the film, moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room,

~~wherein the pixel electrode and the wiring are covered with the resin insulating film without being in contact with the film~~ wherein in the step of moving, the resin insulating film prevents the film from contacting with the wiring, the pixel electrode and the interlayer insulating film.

75. (Currently Amended) A method of manufacturing a light emitting device according to claim 74, wherein the ~~organic~~ insulating material is selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

76. (Currently Amended) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming a wiring over the interlayer insulating film;

forming a pixel electrode ~~connecting~~ connected to the wiring over the interlayer insulating film;

forming a resin insulating film over the wiring, the pixel electrode, and the interlayer insulating film; and

after forming the resin insulating film, forming a film comprising an ~~organic~~ insulating material over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

after forming the film, moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room.

77. (Currently Amended) A method of manufacturing a light emitting device according to claim 76, wherein the ~~organic~~ insulating material is selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

78. (Currently Amended) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming a wiring over the interlayer insulating film;

forming a ~~first~~ pixel electrode ~~connecting~~ connected to the wiring over the interlayer insulating film;

forming a resin insulating film over the wiring, the ~~first~~ pixel electrode, and the interlayer insulating film;

after forming the resin insulating film, forming a film comprising an ~~organic~~ insulating material over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

after forming the film, moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room;

after moving the substrate, removing the film;

after removing the film, forming a bank by etching the resin insulating film ~~to form a bank~~;

baking the bank in a vacuum;

forming an organic compound layer over the bank and the ~~first~~ pixel electrode;

forming a second electrode on the organic compound layer.

79. (Currently Amended) A method of manufacturing a light emitting device according to claim 78, wherein the ~~organic~~ insulating material is selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

80. (Currently Amended) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

performing plasma treatment on a surface of the interlayer insulating film;

forming a contact hole in the interlayer insulating film after performing the plasma treatment;

forming a wiring over the interlayer insulating film;

forming a pixel electrode ~~connecting~~ connected to the wiring over the interlayer insulating film;

forming a resin insulating film over the wiring, the pixel electrode, and the interlayer insulating film; and

after forming the resin insulating film, forming a film over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

after forming the film, moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room.

81. (Currently Amended) A method of manufacturing a light emitting device according to claim 80, wherein the film over the resin insulating film comprises an organic conductive material selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [hydroxyalkyl monoethanolamine], N,N-Bis(2-hydroxyethyl)alkylamine [alkyl diethanolamine], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate, alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzylammonium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

82. (Currently Amended) A method of manufacturing a light emitting device according to claim 80, wherein the film over the resin insulating film comprises an organic insulating material selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

83. (Currently Amended) A method of manufacturing a light emitting device according to claim 50, wherein in the step of ~~forming the protective film~~ moving, ~~the pixel electrode and the wiring are covered with the resin insulating film without being in contact with the film~~ the resin insulating film prevents the protective film from contacting with the wiring, the pixel electrode and the interlayer insulating film.

84. (Currently Amended) A method of manufacturing a light emitting device according to claim 52, wherein in the step of ~~forming the protective film~~ moving, ~~the pixel electrode and the wiring are covered with the resin insulating film without being in contact with the film~~ the resin insulating film prevents the protective film from contacting with the wiring, the pixel electrode and the interlayer insulating film.

85. (Currently Amended) A method of manufacturing a light emitting device according to claim 62, wherein in the step of ~~forming the film~~ moving, ~~the pixel electrode and the wiring are covered with the resin insulating film without being in contact with the film~~ the

resin insulating film prevents the film over the resin insulating film from contacting with the wiring, the pixel electrode and the interlayer insulating film.

86. (Currently Amended) A method of manufacturing a light emitting device according to claim 65, wherein in the step of ~~forming the film~~ moving, ~~the pixel electrode and the wiring are covered with the resin insulating film without being in contact with the film~~ the resin insulating film prevents the film over the resin insulating film from contacting with the wiring, the pixel electrode and the interlayer insulating film.

87. (Currently Amended) A method of manufacturing a light emitting device according to claim 70, wherein in the step of ~~forming the film~~ moving, ~~the pixel electrode and the wiring are covered with the resin insulating film without being in contact with the film~~ the resin insulating film prevents the film comprising the conductive material from contacting with the wiring, the pixel electrode and the interlayer insulating film.

88. (Currently Amended) A method of manufacturing a light emitting device according to claim 72, wherein in the step of ~~forming the film~~ moving, ~~the pixel electrode and the wiring are covered with the resin insulating film without being in contact with the film~~ the resin insulating film prevents the film comprising the conductive material from contacting with the wiring, the pixel electrode and the interlayer insulating film.

89. (Currently Amended) A method of manufacturing a light emitting device according to claim 76, wherein in the step of ~~forming the film~~ moving, ~~the pixel electrode and the wiring are covered with the resin insulating film without being in contact with the film~~ the resin insulating film prevents the film comprising the insulating material from contacting with the wiring, the pixel electrode and the interlayer insulating film.

90. (Currently Amended) A method of manufacturing a light emitting device according to claim 78, wherein in the step of ~~forming the film~~ moving, ~~the pixel electrode and the wiring are covered with the resin insulating film without being in contact with the film~~ the

resin insulating film prevents the film comprising the insulating material from contacting with the wiring, the pixel electrode and the interlayer insulating film.

91. (Currently Amended) A method of manufacturing a light emitting device according to claim 80, wherein in the step of ~~forming the film~~ moving, ~~the pixel electrode and the wiring are covered with the resin insulating film without being in contact with the film~~ the resin insulating film prevents the film over the resin insulating film from contacting with the wiring, the pixel electrode and the interlayer insulating film.